

Abstract of the Disclosure

An n-contact layer, an n-cladding layer, an MQW active layer, and a p-first cladding layer are formed in this order on a sapphire substrate. An n-current blocking layer having a striped opening is formed on the p-first cladding layer. The width of the striped opening gradually increases from W2 to W1 as the depth thereof decreases from a lower layer to an upper layer in the current blocking layer. A p-second cladding layer is formed on the n-current blocking layer and on the p-first cladding layer inside the striped opening. The p-second cladding layer comprises a lower layer having the width W2 at its lower end and an upper layer having a width W1 larger than the width W2.